

1 ABSTRACT OF THE DISCLOSURE

2 In one aspect, the invention includes an etching process,
3 comprising: a) providing a first material over a substrate, the first
4 material comprising from about 2% to about 20% carbon (by weight);
5 b) providing a second material over the first material; and c) etching
6 the second material at a faster rate than the first material. In another
7 aspect, the invention includes a capacitor forming method, comprising:
8 a) forming a wordline over a substrate; b) defining a node proximate
9 the wordline; c) forming an etch stop layer over the wordline, the etch
10 stop layer comprising carbon; d) forming an insulative layer over the
11 etch stop layer; e) etching through the insulative layer to the etch stop
12 layer to form an opening through the insulative layer; and e) forming
13 a capacitor construction comprising a storage node, dielectric layer and
14 second electrode, at least a portion of the capacitor construction being
15 within the opening. In yet another aspect, the invention includes a
16 semiconductive material assembly, comprising: a) a semiconductive
17 substrate; and b) a layer over the semiconductive substrate, the layer
18 comprising silicon, nitrogen and carbon.

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